

## TK50P03M1-VB Datasheet

### P-Channel 30 V (D-S) MOSFET

#### PRODUCT SUMMARY

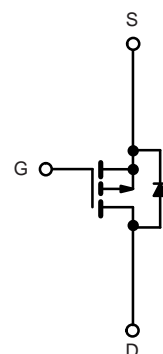
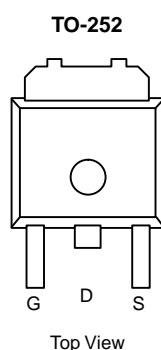
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>
- 30	0.011 at $V_{GS} = -10$ V	-60
	0.013 at $V_{GS} = -4.5$ V	-55

#### FEATURES

- Compliant to RoHS Directive 2002/95/EC



Available  
**RoHS\***  
 COMPLIANT



P-Channel MOSFET

#### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current ( $T_J = 175$ °C)	$I_D$	$T_C = 25$ °C	A
		$T_C = 125$ °C	
Pulsed Drain Current	$I_{DM}$	- 240	
Avalanche Current	$I_{AR}$	- 50	
Repetitive Avalanche Energy <sup>b</sup>	$E_{AR}$	180	mJ
Power Dissipation	$P_D$	$T_C = 25$ °C (TO-220AB and TO-263)	W
		$T_A = 25$ °C (TO-263) <sup>c</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 175	°C

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	$R_{thJA}$	PCB Mount (TO-263) <sup>c</sup>	°C/W
		Free Air (TO-220AB)	
Junction-to-Case	$R_{thJC}$	0.8	

Notes:

a. Package limited.

b. Duty cycle  $\leq 1$  %.

c. When mounted on 1" square PCB (FR-4 material).

d. See SOA curve for voltage derating.

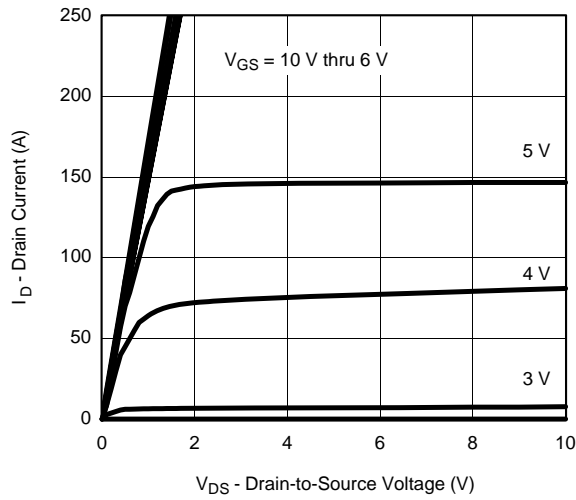
\* Pb containing terminations are not RoHS compliant, exemptions may apply.

SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 30			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1		- 3	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V			- 1	μA
		V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			- 50	
		V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			- 250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 120			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 30 A		0.011		Ω
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 30 A, T <sub>J</sub> = 125 °C		0.015		
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 30 A, T <sub>J</sub> = 175 °C		0.019		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 20 A		0.013		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 75 A	20			S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = - 25 V, f = 1 MHz		3300		pF
Output Capacitance	C <sub>oss</sub>			1565		
Reversen Transfer Capacitance	C <sub>rss</sub>			715		
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 75 A		160	240	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>			32		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			30		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = - 15 V, R <sub>L</sub> = 0.2 Ω I <sub>D</sub> ≡ - 75 A, V <sub>GEN</sub> = - 10 V, R <sub>g</sub> = 2.5 Ω		25	40	ns
Rise Time <sup>c</sup>	t <sub>r</sub>			225	360	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			150	240	
Fall Time <sup>c</sup>	t <sub>f</sub>			210	340	
Source-Drain Diode Ratings and Characteristics <sup>b</sup> (T <sub>C</sub> = 25 °C)						
Continuous Current	I <sub>S</sub>				- 60	A
Pulsed Current	I <sub>SM</sub>				- 240	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 75 A, V <sub>GS</sub> = 0 V		- 1.2	- 1.5	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 75 A, dI/dt = 100 A/μs		55	100	ns
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>			2.5	5	A
Reverse Recovery Charge	Q <sub>rr</sub>			0.07	0.25	μC

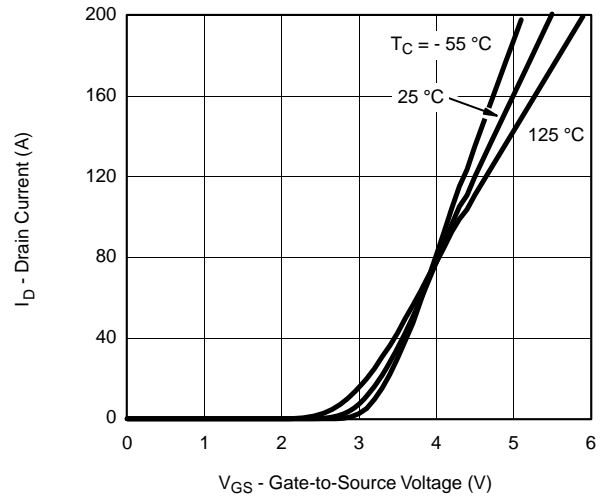
Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.  
c. Independent of operating temperature.

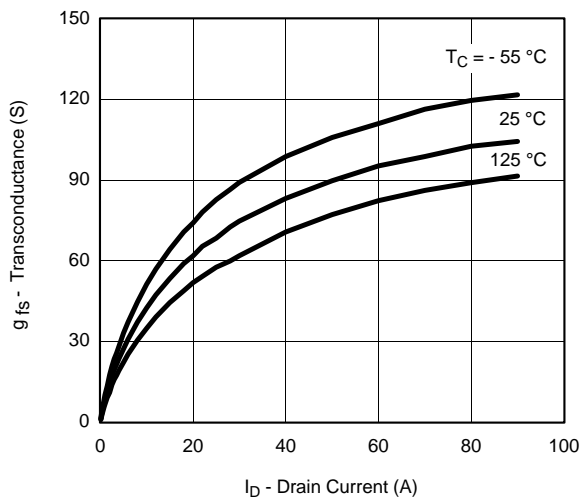
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)


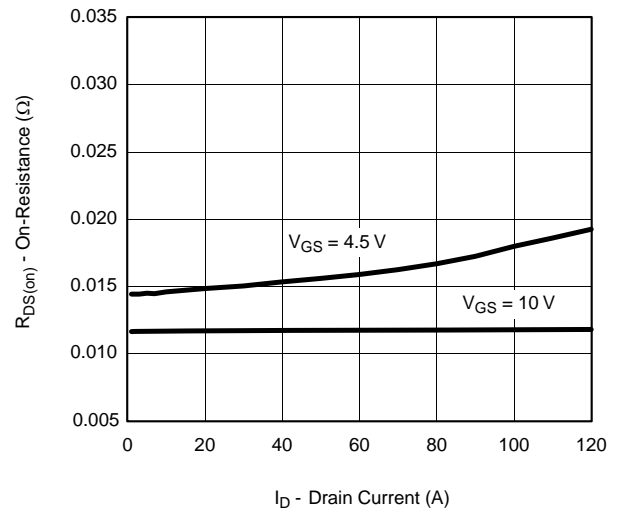
Output Characteristics



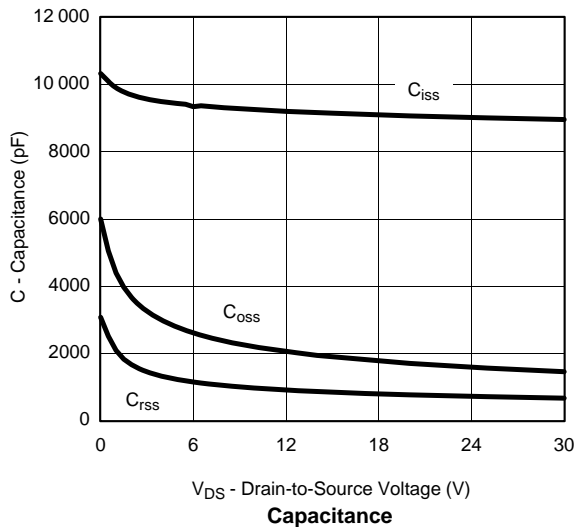
Transfer Characteristics



Transconductance



On-Resistance vs. Drain Current

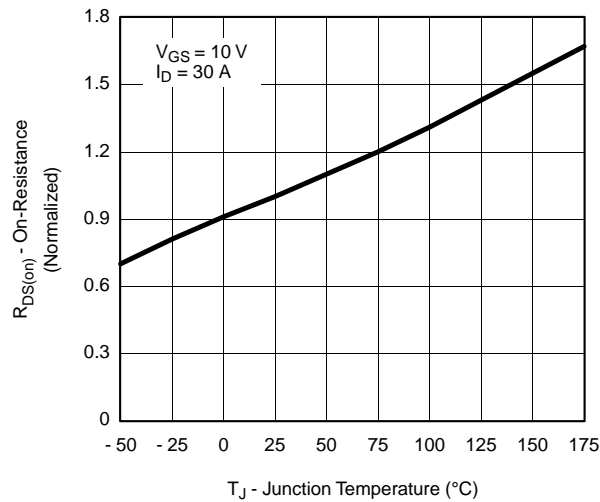


Capacitance

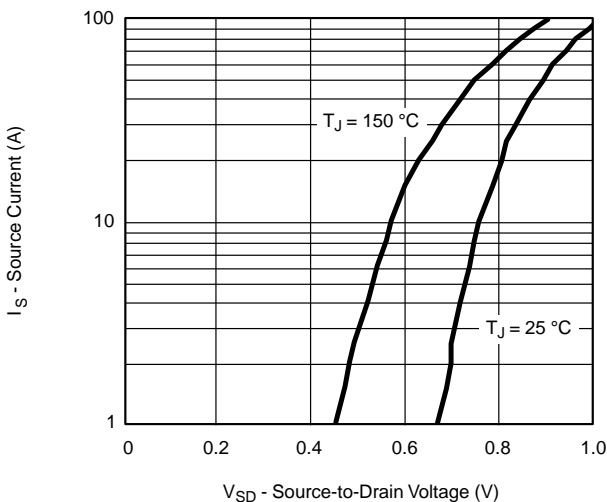


Gate Charge

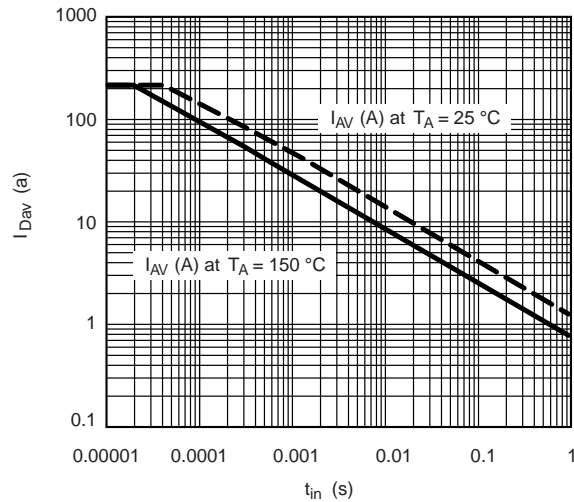
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



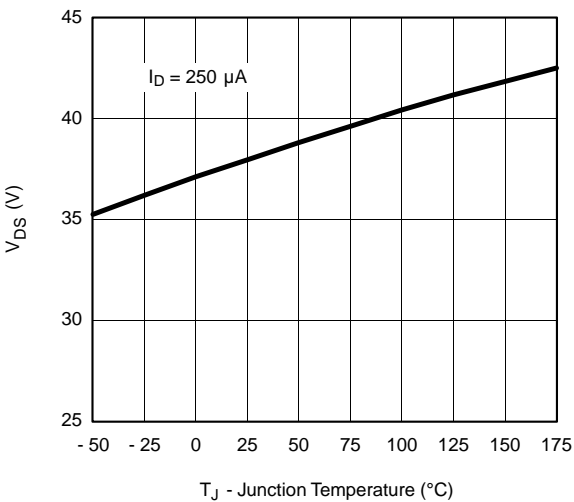
**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**

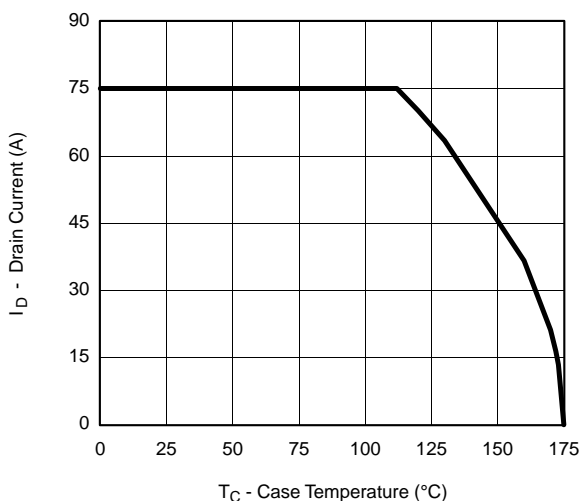


**Avalanche Current vs. Time**

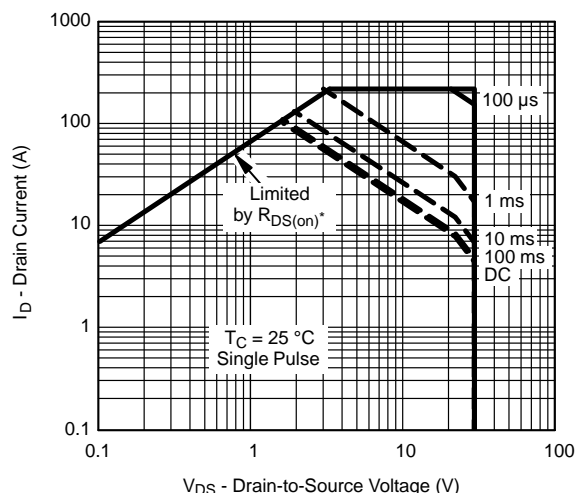


**Drain Source Breakdown vs. Junction Temperature**

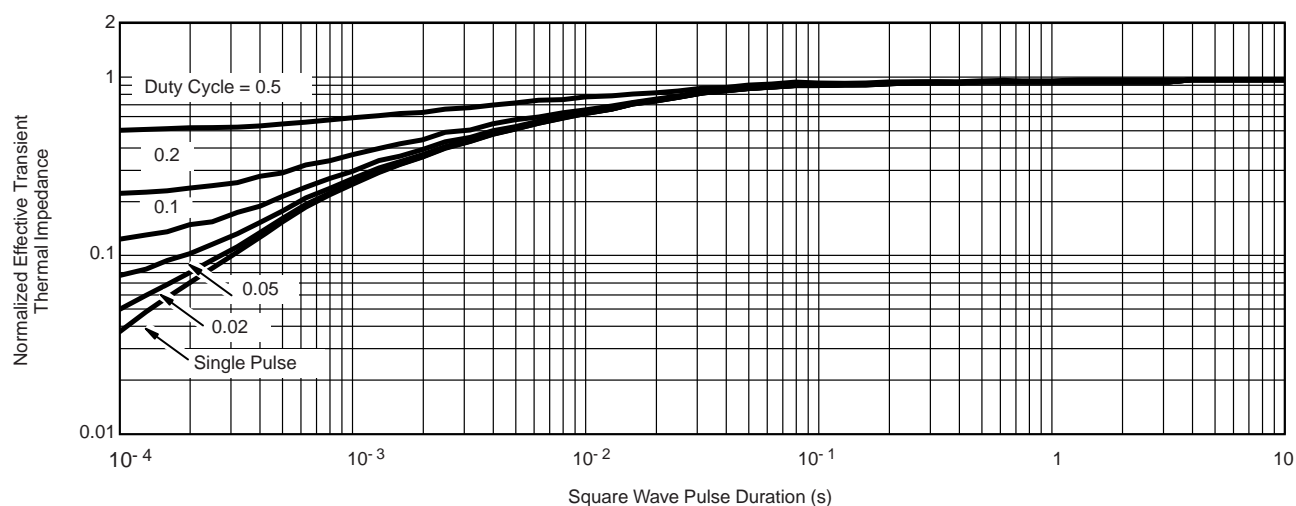
## THERMAL RATINGS



**Maximum Avalanche and Drain Current  
vs. Case Temperature**

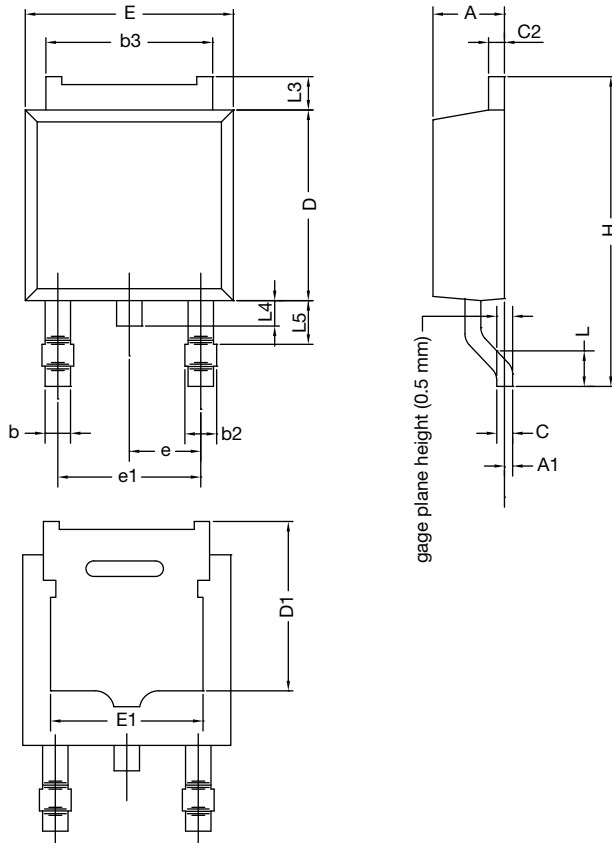


**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Case**

## TO-252AA CASE OUTLINE

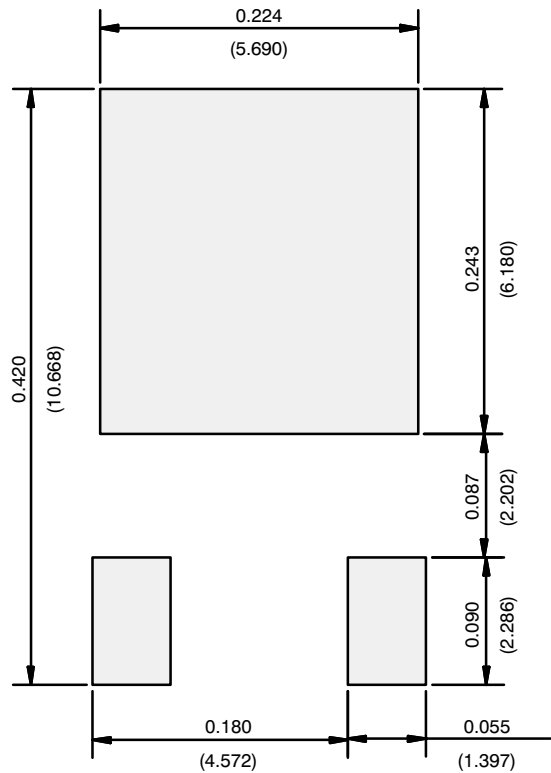


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12				
DWG: 5347				

### Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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